NTE ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE127
Germanium PNP Transistor
Horizontal Output Amplifier

Absolute Maximum Ratings:

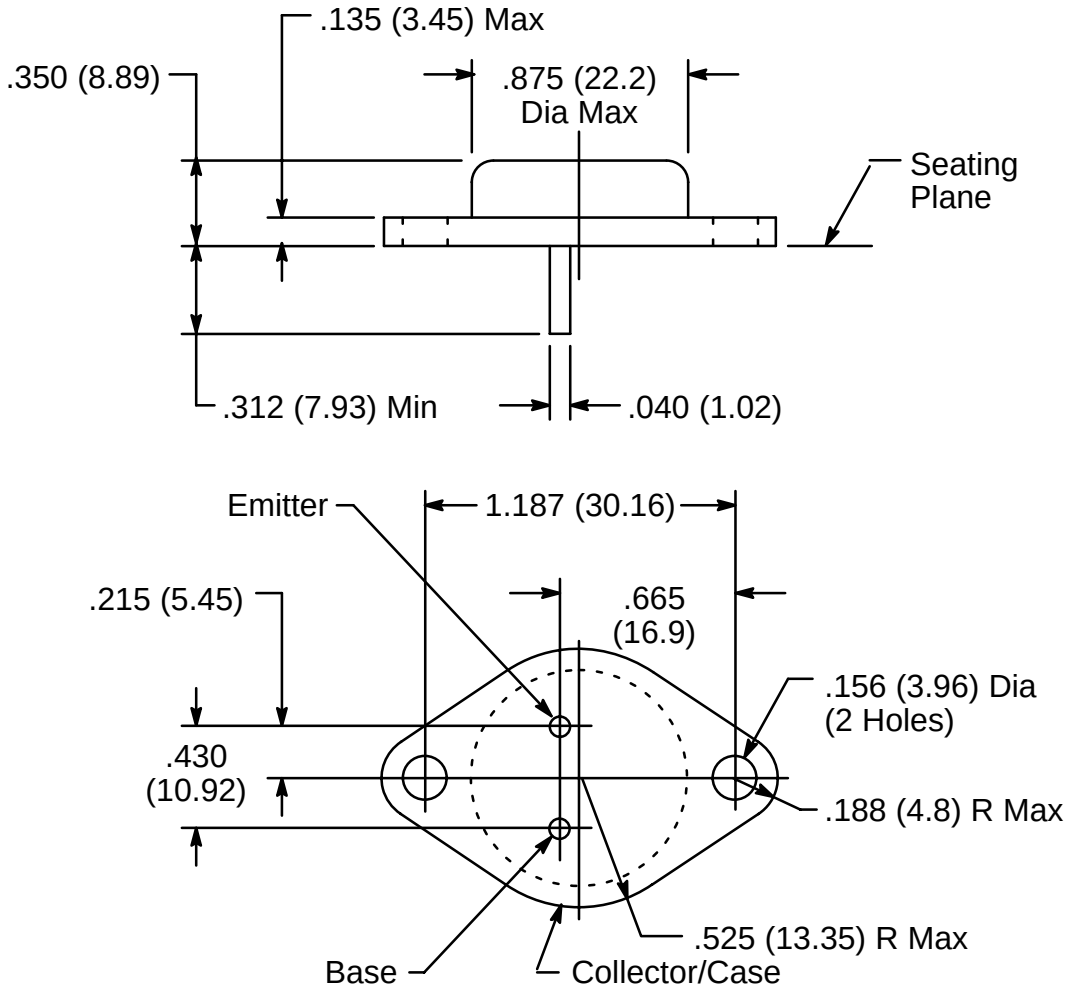
Collector–Base Voltage, V_{CBO}
- Peak 320V
- Continuous 60V

Emitter–Base Voltage, V_{EBO} 2V
Collector Current, I_C 10A
Base Current, I_B . . . . . +4, –1A
Power Dissipation ($T_{MF} \le +55°C$), P_D 5W
Operating Junction Temperature Range, $T_J(opr)$ . . . . . –65° to +85°C
Storage Temperature Range, T_{stg} . . . . . –65° to +85°C
Maximum Thermal Resistance, Junction–to–Case, R_{thJC} . . . . . 1.5°C/W
Lead Temperature (During Soldering, 10sec Max), T_L . . . . . +230°C

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Breakdown Voltage	$V_{(BR)CES}$	I_C = 0.025A, V_{EB} = 0	320	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 100mA, I_C = 0	2	–	–	V
Collector Cutoff Current	I_{CBO}	V_{CB} = 10V, I_E = 0	–	–	200	μA
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 6A, I_B = 400mA	–	–	1.5	V
		I_C = 3A, I_B = 200mA	–	–	1.5	V
DC Current Gain	h_{FE}	V_{CE} = 3V, I_C = 6A	15	–	–	
Base–Emitter Voltage	V_{BE}	I_C = 6A, I_B = 400mA	–	0.8	–	V
Turn–Off Time	$t_s + t_f$		–	–	1.2	μs

Note 1. This device is for **replacement only** and ***NOT*** intended for new design. Therefore, these specifications are for **reference only** and strictly for determining the suitability of this device as a replacement in a working circuit.


.135 (3.45) Max
.350 (8.89)
.875 (22.2)
Dia Max
Seating
Plane
.312 (7.93) Min
.040 (1.02)
Emitter
1.187 (30.16)
.215 (5.45)
.665
(16.9)
.156 (3.96) Dia
(2 Holes)
.430
(10.92)
.188 (4.8) R Max
.525 (13.35) R Max
Base
Collector/Case